

Ripple carry adder (RCA)

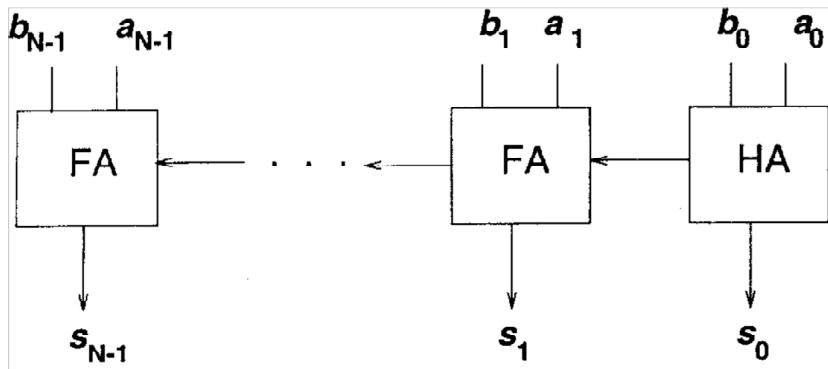
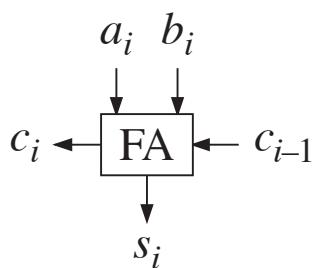


Fig. 1. Ripple carry adder.

Carry acceleration

- Consider an FA operation
- Investigate carry function



a_i	b_i	c_i	Function
0	0	0	Kill
0	1	c_{i-1}	Propagate
1	0	c_{i-1}	Propagate
1	1	1	Generate

- Rewrite carry function

$$c_i = a_i b_i + (a_i \oplus b_i) c_{i-1} = G_i + P_i c_{i-1}$$

Note that G_i and P_i do only depend on the input

Manchester carry chain adder (MCC)

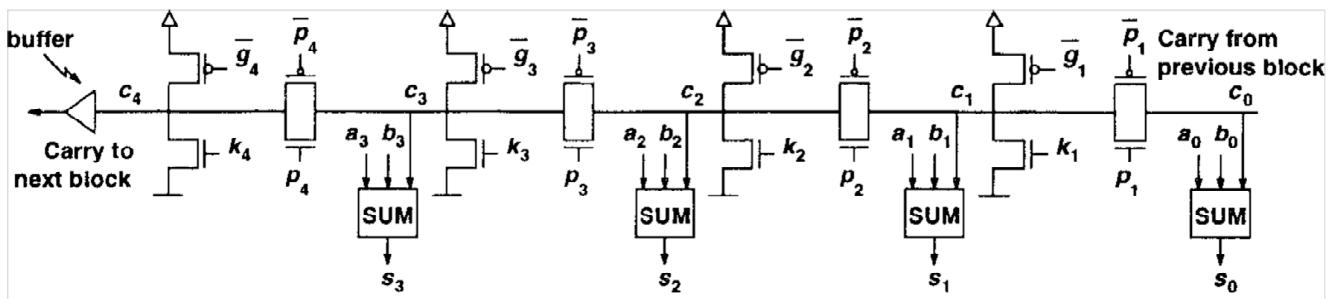


Fig. 3. A 4-b block of a Manchester Carry Chain Adder.

Carry skip adder (CSK/VSK)

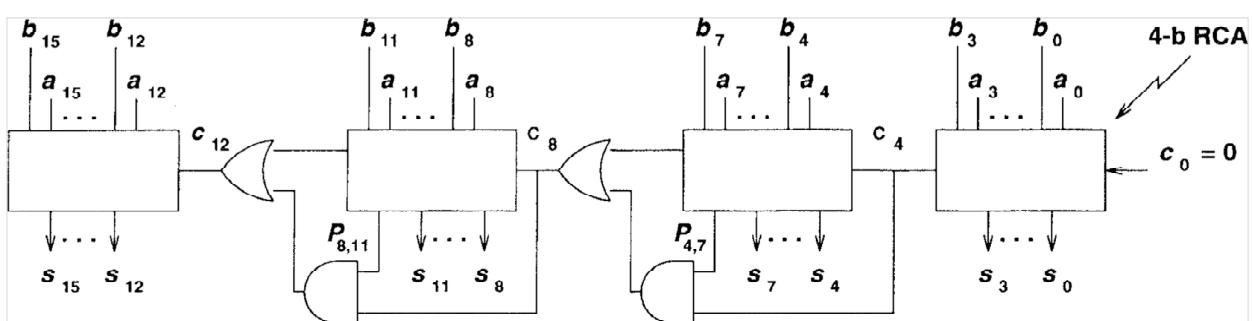


Fig. 4. A 16-b Carry Skip Adder.

Carry select adder (CSL)

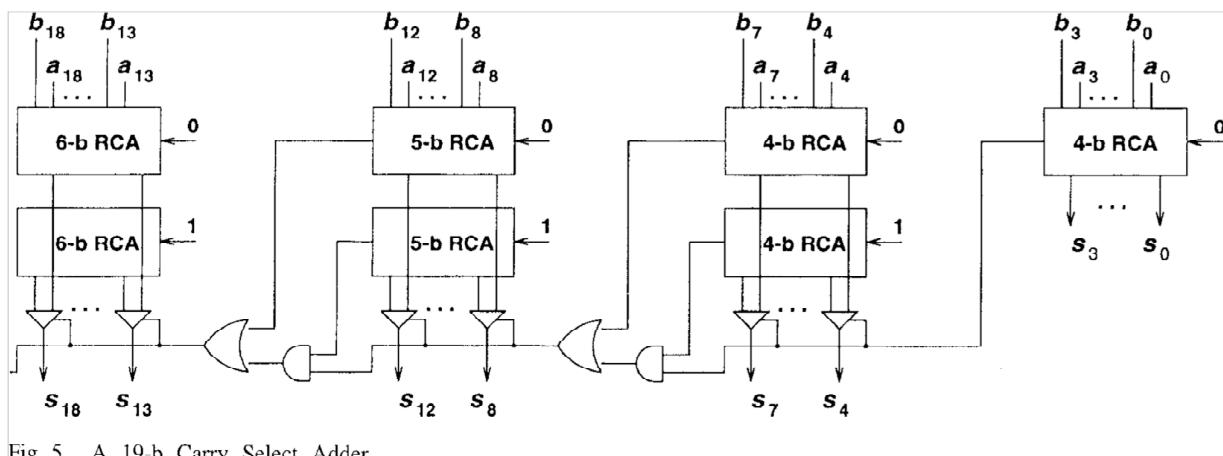


Fig. 5. A 19-b Carry Select Adder.

Carry look-ahead adder (CLA)

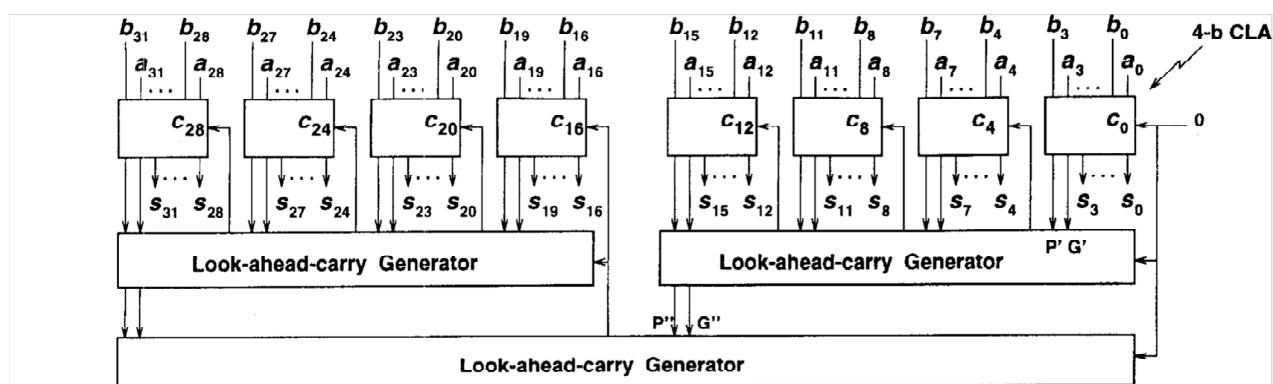


Fig. 6. A 32-b Carry Lookahead Adder.

CLA with high regularity — ELM

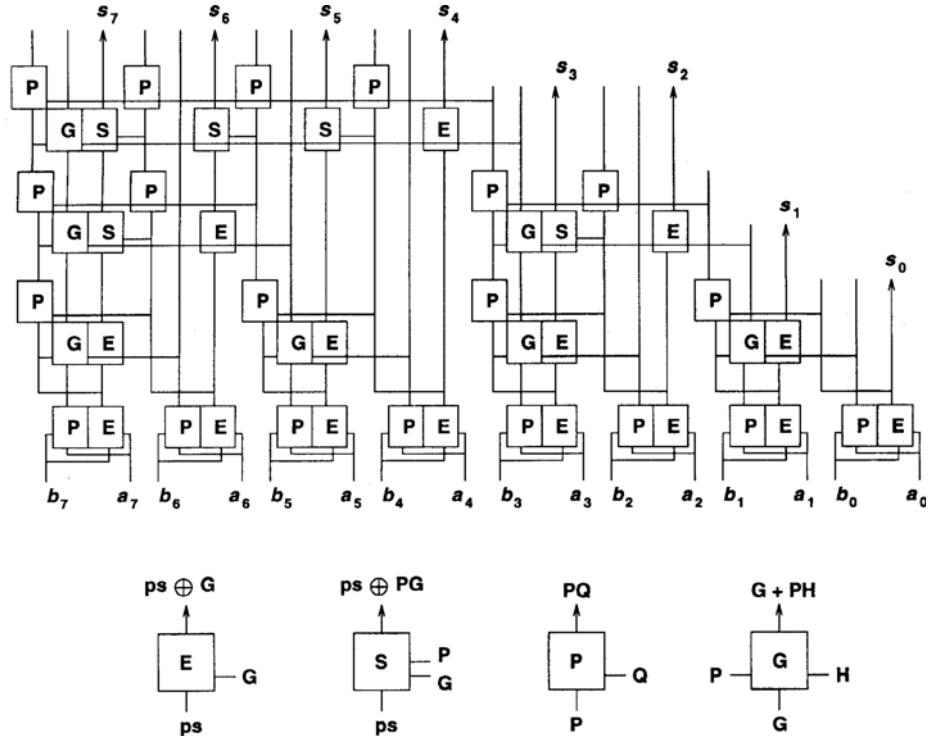


Fig. 7. An 8-b ELM adder.

Signed-digit addition

- Use a signed-digit number system with
 - digits $d_i \in \{-\alpha, \dots, -1, 0, 1, \dots, \alpha\}$
 - base $r \geq 3$
 - value $D = \sum_{i=0}^{k-1} d_i r^i$
- Addition algorithm

Signed Digit Addition (A, B, S)	
For $i = 0$ to m do	
1.	Compute a temporary sum digit $p_i = a_i + b_i$.
2.	Compute an interim sum digit u_i and a carry digit c_{i+1} : $r \cdot c_{i+1} + u_i = p_i$ such that $ u_i \leq r - 2$ and $ c_{i+1} \leq 1$.
3.	Compute the final sum: $s_i = u_i + c_{i+1}$.

Fig. 8. The radix-r OSD addition algorithm.

Signed-digit adder (SD-r)

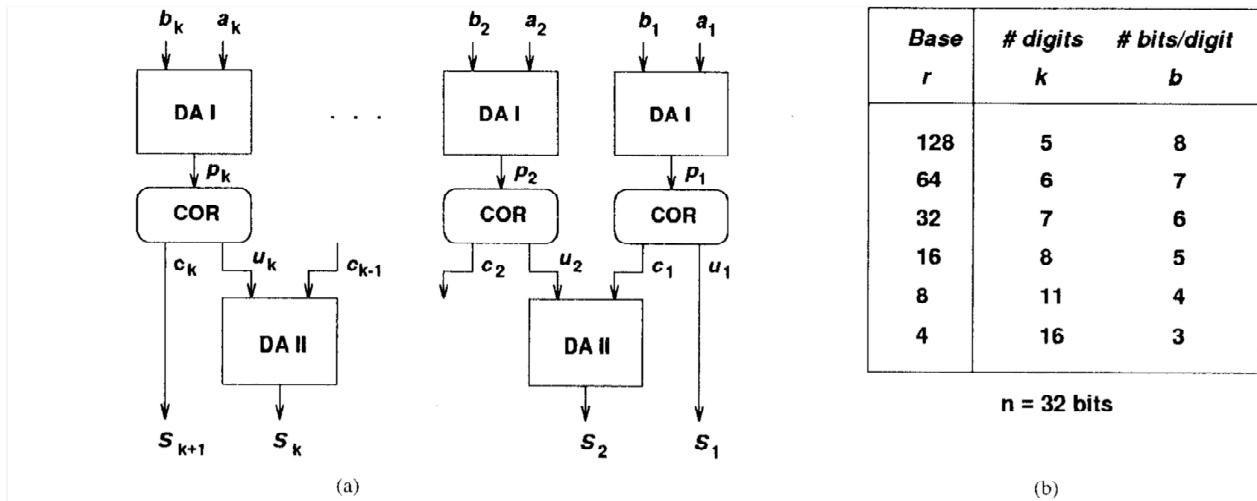


Fig. 9. Signed digit adder. (a) SDA. (b) Values of k and b for different r .

Carry-save addition (CSA)

- Represent A with a sum vector AS and a carry vector AC

$$A = \sum_{i=0}^n (ac_i + as_i)r^i$$

- Add numbers without propagating the carry

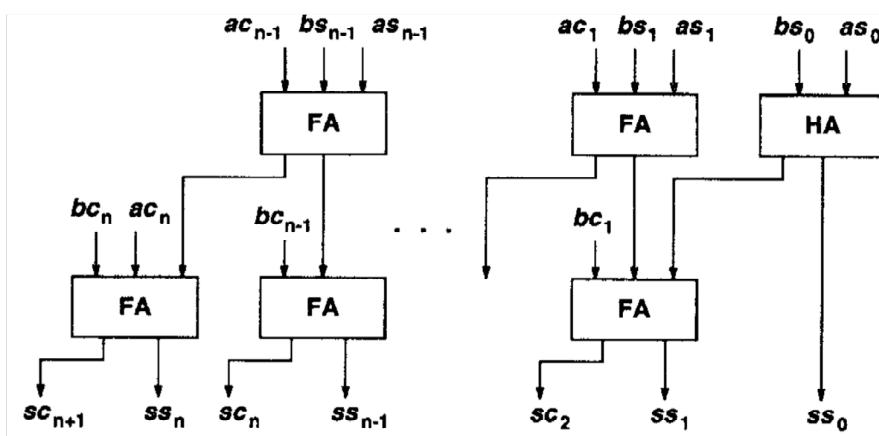


Fig. 10. Carry save adder.

Adder experiment

- Automatic layout generation for gate matrix with in-house tool
- Power estimation with HSPICE

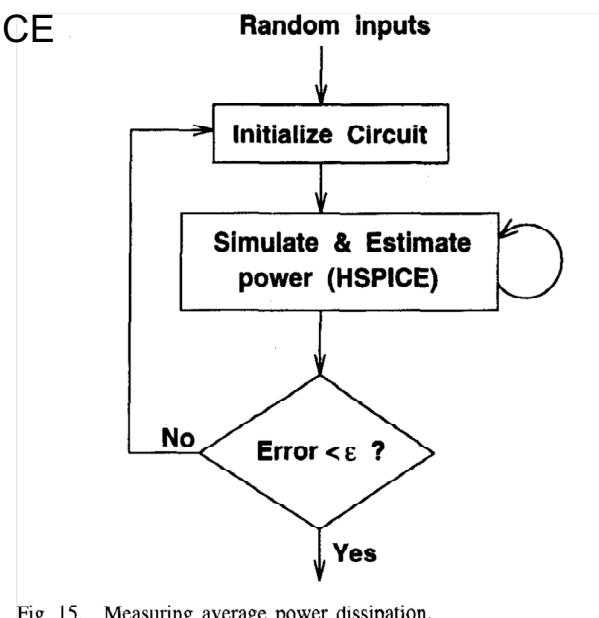


Fig. 15. Measuring average power dissipation.

Transistors and area in the adder circuits

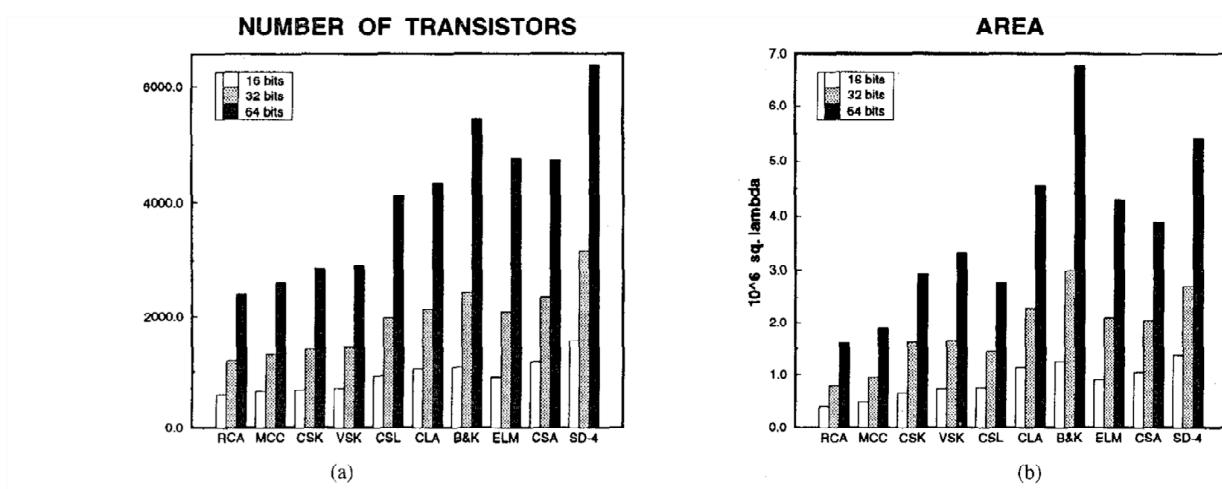


Fig. 13. (a) Number of transistors. (b) Area.

Delay of the adder circuits

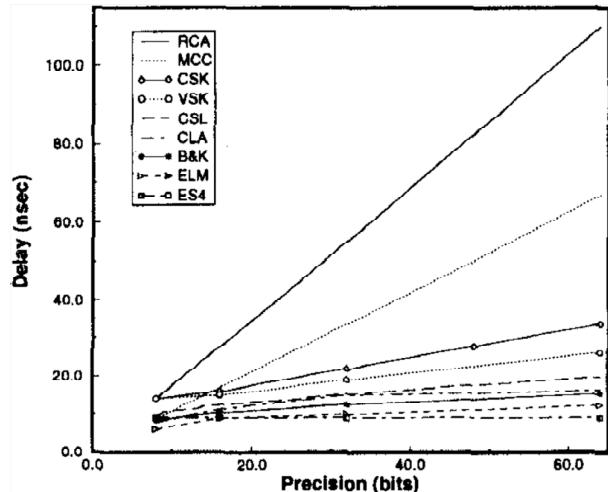
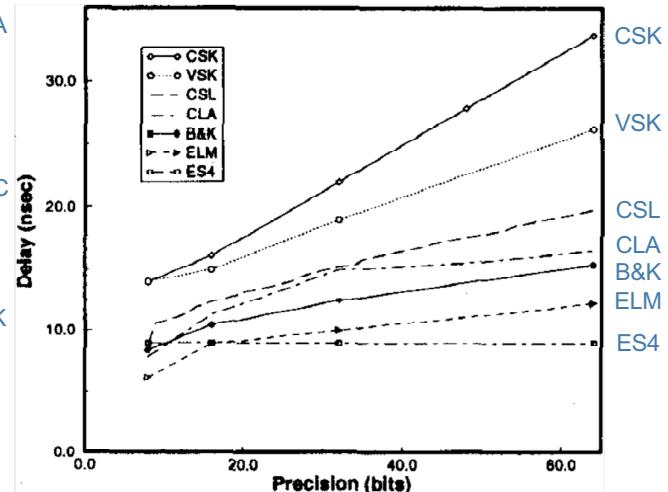


Fig. 21 (a) Delay with precision



(b) Detail of the faster adders

P consumption of the adder circuits

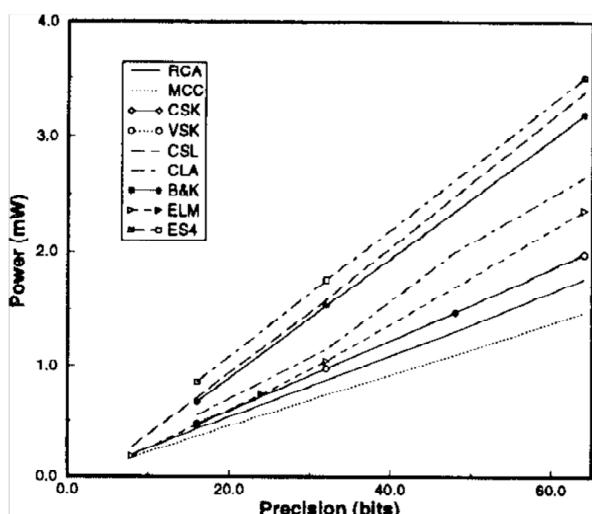
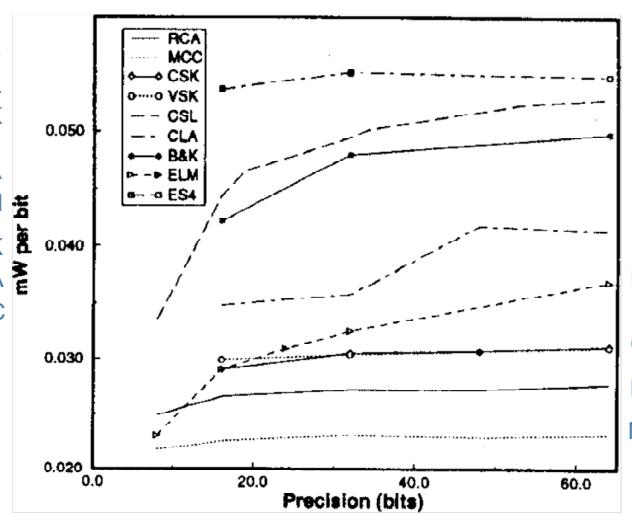


Fig. 21 (a) P with precision



(b) P per bit

PDP of the adder circuits

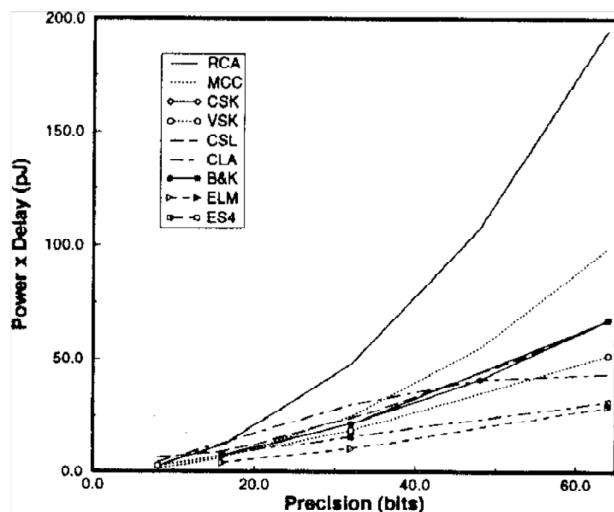
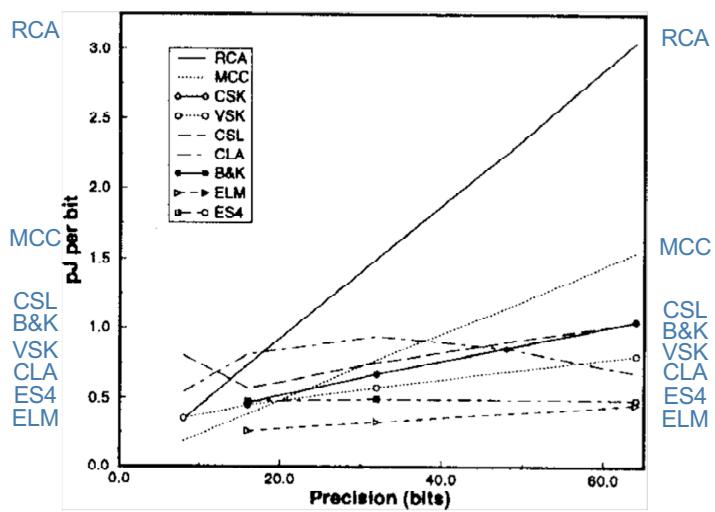


Fig. 22 (a) $P^*\text{delay}$ with precision



(b) $P^*\text{delay per bit}$

Sub- V_T leakage in memories

- Leakage in SRAM cell

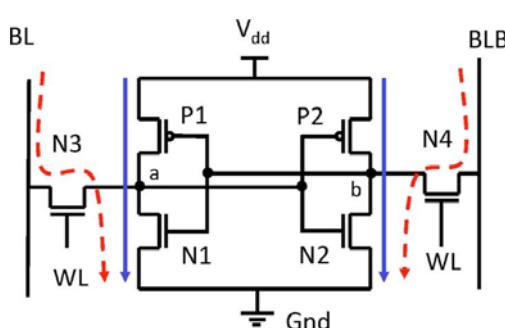


Fig. 2

- Worst case bitline leakage

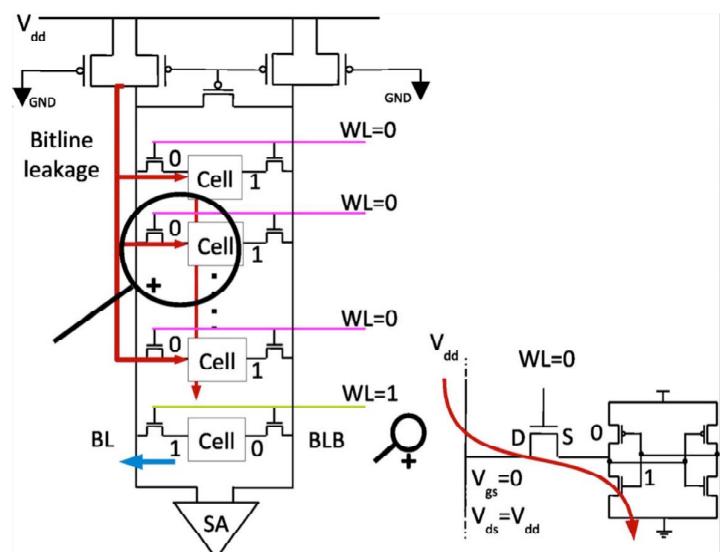


Fig. 4

Bitline design

- Precharge BL to low

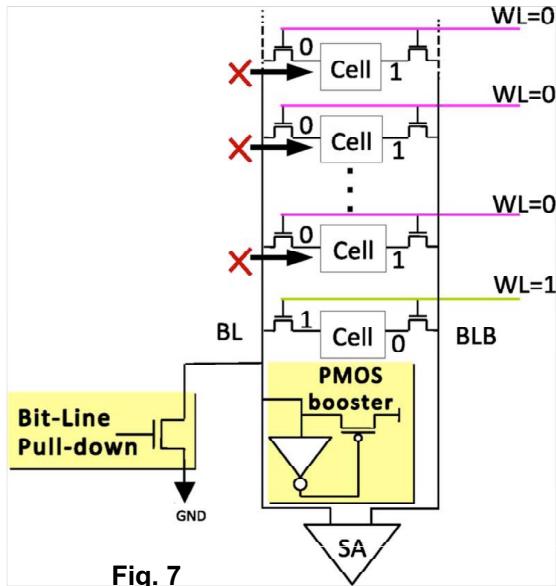


Fig. 7

- $V_{GS} < 0$ reduces leakage

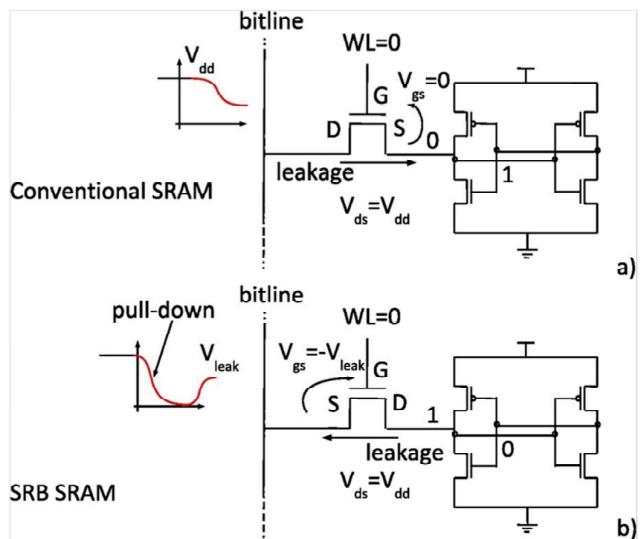


Fig. 8

Wordline design

- Negative voltage of wordline reduces leakage

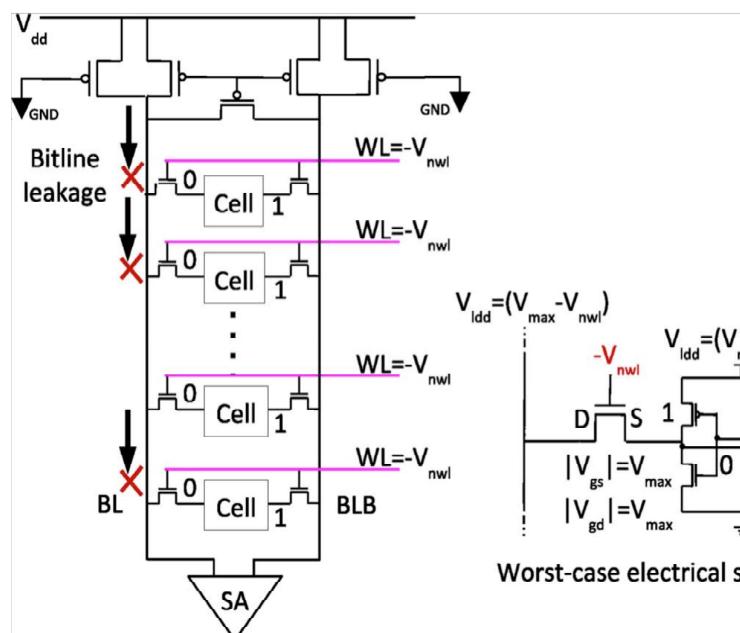


Fig. 10

Power gating

- High- V_T sleep transistor

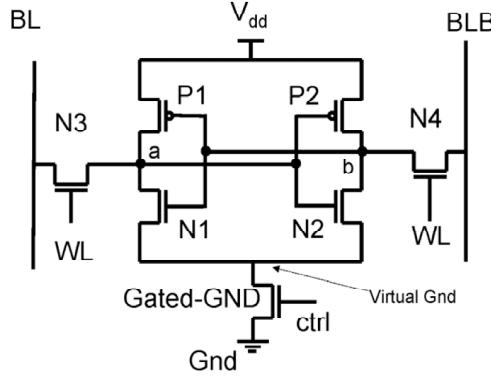


Fig. 15

- Dynamic voltage scaling

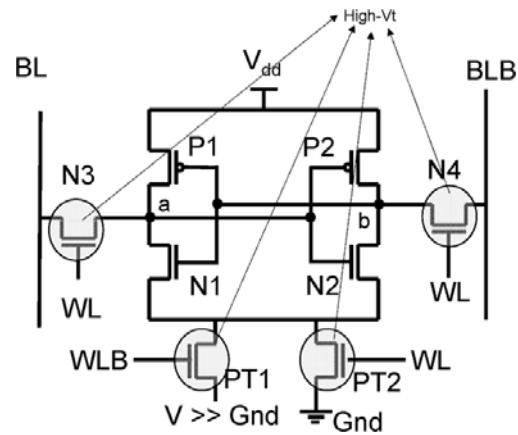


Fig. 17

Asymmetric bitcell design

- Use preferred state, e.g. 0, to reduce leakage

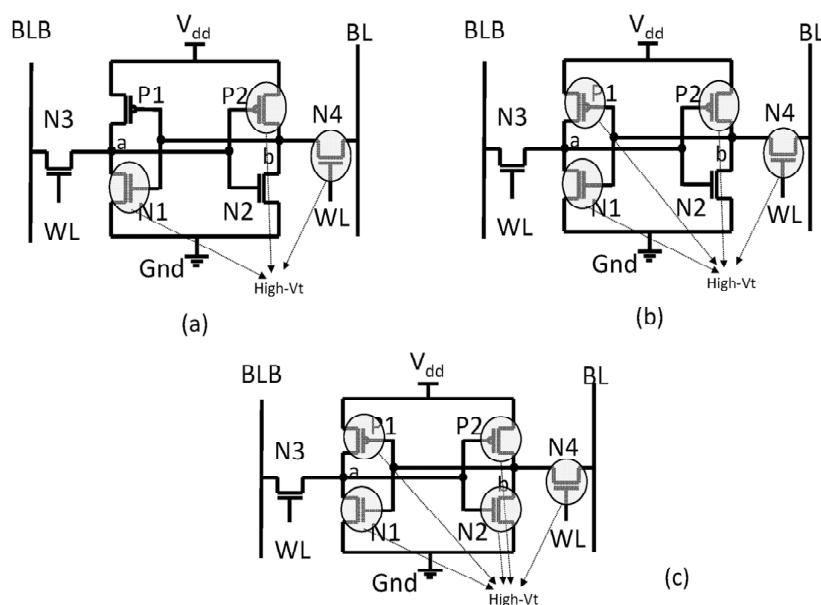


Fig. 12

SRAM cell body-bias

- Controlling V_T of SRAM cell

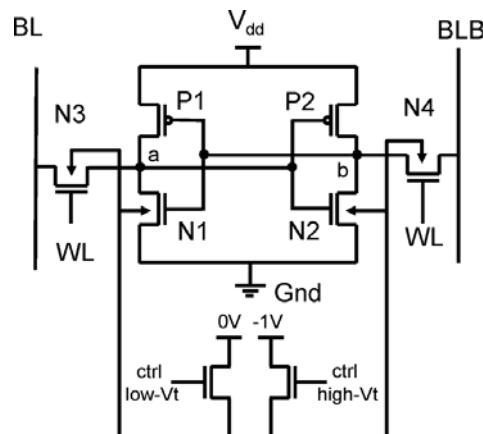


Fig. 18

Power, variability, and scalability results

- Comparison of leakage reduction strategies

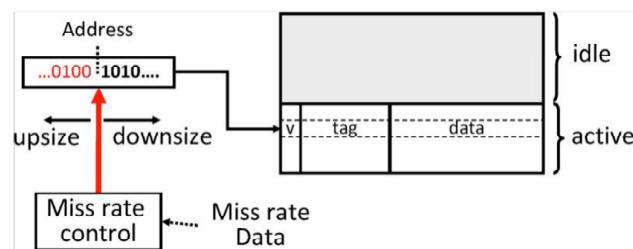
Strategy	LP	Robustness	Scalability
Power gating	++	+++	+++
Body-biasing	+++	++	+
Wordline design	+	++	+++
Bitcell design	+++	+	+
Bitline design	+	+	+++
Dynamic V_{DD} scaling	++	+	+

Reorganized Table IV

Cache memory

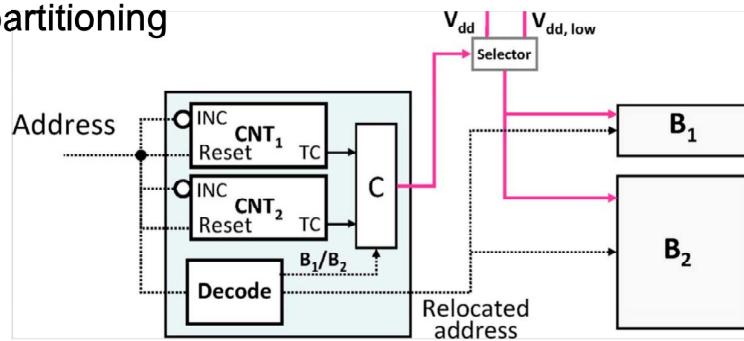
- Resizable cache

Fig. 27



- Multibank partitioning

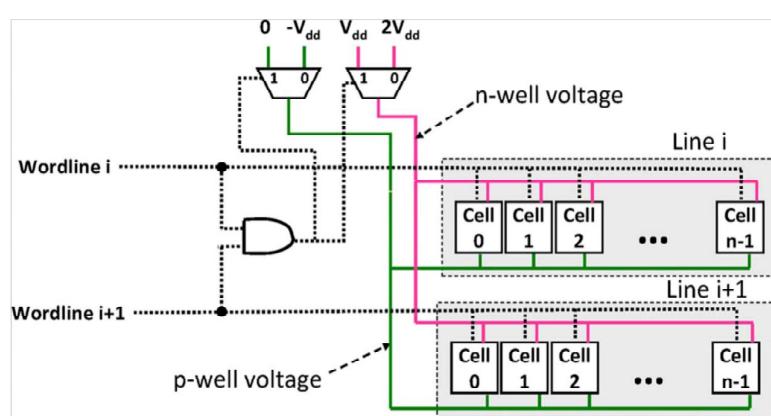
Fig. 28



Cache memory body-bias

- Controlling V_T of cache lines

Fig. 26



References

10.pdf Area-time-power tradeoffs in parallel adders

C. Nagendra, M.J. Irwin, and R.M. Owens

IEEE Transactions on Circuits and Systems II: Analog and Digital Signal Processing, volume 43, issue 10, Oct. 1996, pages 689-702

11.pdf Design techniques and architectures for low-leakage SRAMs

A. Calimera, A. Macii, E. Macii, and M. Poncino

IEEE Transactions on Circuits and Systems I: Regular Papers, volume 59, issue 9, Sep. 2012, pages 1992-2007